

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A film formation method comprising the steps of:
forming a first film on an electrode provided in a chamber by a CVD method using a first gas;
installing a substrate into the chamber after forming the first film; and
forming a second film over a surface of the substrate by a sputtering method using the first film as a target and a second gas in the chamber.
2. (Original) A film formation method according to claim 1, wherein the second film is formed at a pressure of 20 Pa or less.
3. (Original) A film formation method according to claim 1, wherein the second film is formed over one selected from the group consisting of a glass substrate, a plastic substrate, and an organic resin film.
4. (Canceled)
5. (Original) A film formation method according to claim 1, wherein a semiconductor device is manufactured by using the second film as a protective film of a semiconductor element.
6. (Previously Presented) A film formation method according to claim 5, wherein the semiconductor element comprises at least one selected from the group consisting of a thin film transistor, an organic thin film transistor, a thin film diode, a photoelectric conversion element, and a resistor.
7. (Previously Presented) A film formation method comprising the steps of:
forming a first film on an electrode provided in a chamber by a CVD method using a first gas;

installing a substrate into the chamber after forming the first film; and
forming a silicon nitride film over a surface of the substrate by a sputtering method
using the first film as a target and a second gas in the chamber.

8. (Original) A film formation method according to claim 7, wherein the first gas
comprises a silicide gas and nitrogen.

9. (Original) A film formation method according to claim 7, wherein the second gas
comprises at least one selected from the group consisting of helium (He), neon (Ne), argon
(Ar), krypton (Kr), and xenon (Xe).

10. (Previously Presented) A film formation method according to claim 7, wherein the
silicon nitride film is formed at a pressure of 20 Pa or less.

11. (Original) A film formation method according to claim 7, wherein the second film
is formed over one selected from the group consisting of a glass substrate, a plastic substrate,
and an organic resin film.

12. (Canceled)

13. (Original) A film formation method according to claim 8, wherein the silicide gas
comprises at least one selected from the group consisting of monosilane, disilane, and
trisilane.

14. (Previously Presented) A film formation method according to claim 7, wherein a
semiconductor device is manufactured by using the silicon nitride film as a protective film of
a semiconductor element.

15. (Previously Presented) A film formation method according to claim 14, wherein
the semiconductor element comprises at least one selected from the group consisting of a thin
film transistor, an organic thin film transistor, a thin film diode, a photoelectric conversion
element, and a resistor.

16.-33. (Canceled)

34. (Previously Presented) A method for manufacturing a semiconductor device comprising:

forming a thin film transistor over a substrate, wherein the thin film transistor comprises an active region and a gate electrode with a gate insulating film interposed therebetween;

forming a first film on an electrode provided in a chamber by a CVD method using a first gas;

installing the substrate into the chamber after forming the first film; and

forming a second film over the thin film transistor by a sputtering method using the first film as a target and a second gas in the chamber.

35. (Previously Presented) A method for manufacturing a semiconductor device according to claim 34, wherein the second film is formed at a pressure of 20 Pa or less.

36. (Previously Presented) A method for manufacturing a semiconductor device according to claim 34, wherein the substrate comprises at least one selected from the group consisting of a glass substrate, a plastic substrate, and an organic resin film.

37. (Canceled)

38. (Previously Presented) A method for manufacturing a semiconductor device according to claim 34, further comprising a step of forming an EL layer and an electrode over the second film.

39. (Previously Presented) A method for manufacturing a semiconductor device comprising:

forming a thin film transistor over a substrate, wherein the thin film transistor comprises an active region and a gate electrode with a gate insulating film interposed therebetween;

forming a first film on an electrode provided in a chamber by a CVD method using a first gas;

installing the substrate into the chamber after forming the first film; and

forming a silicon nitride film over the thin film transistor by a sputtering method using the first film as a target and a second gas in the chamber.

40. (Previously Presented) A method for manufacturing a semiconductor device according to claim 39, wherein the first gas comprises a silicide gas and nitrogen.

41. (Previously Presented) A method for manufacturing a semiconductor device according to claim 40, wherein the silicide gas comprises at least one selected from the group consisting of monosilane, disilane, and trisilane.

42. (Previously Presented) A method for manufacturing a semiconductor device according to claim 39, wherein the second gas comprises at least one selected from the group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

43. (Previously Presented) A method for manufacturing a semiconductor device according to claim 39, wherein the second film is formed at a pressure of 20 Pa or less.

44. (Previously Presented) A method for manufacturing a semiconductor device according to claim 39, wherein the substrate comprises at least one selected from the group consisting of a glass substrate, a plastic substrate, and an organic resin film.

45. (Canceled)

46. (Previously Presented) A method for manufacturing a semiconductor device according to claim 39, further comprising a step of forming an EL layer and an electrode over the second film.

47.-62. (Canceled)

63. (Previously Presented) A film formation method comprising the steps of:
forming a first film on an electrode provided in a chamber by a CVD method using a
first gas;
installing a substrate into the chamber after forming the first film; and
forming a silicon nitride film over a surface of the substrate by a sputtering method
using the first film as a target and a second gas in the chamber.

64. (Previously Presented) A film formation method according to claim 63, wherein
the first gas comprises a silicide gas and nitrogen.

65. (Previously Presented) A film formation method according to claim 63, wherein
the second gas comprises at least one selected from the group consisting of helium (He), neon
(Ne), argon (Ar), krypton (Kr), and xenon (Xe).

66. (Previously Presented) A film formation method according to claim 63, wherein
the silicon nitride film is formed at a pressure of 20 Pa or less.

67. (Previously Presented) A film formation method according to claim 63, wherein
the silicon nitride film is formed over one selected from the group consisting of a glass
substrate, a plastic substrate, and an organic resin film.

68. (Canceled)

69. (Previously Presented) A film formation method according to claim 64, wherein
the silicide gas comprises at least one selected from the group consisting of monosilane,
disilane, and trisilane.

70. (Previously Presented) A film formation method according to claim 63, wherein a
semiconductor device is manufactured by using the silicon nitride film as a protective film of
a semiconductor element.

71. (Previously Presented) A film formation method according to claim 70, wherein

the semiconductor element comprises at least one selected from the group consisting of a thin film transistor, an organic thin film transistor, a thin film diode, a photoelectric conversion element, and a resistor.

72. (Previously Presented) A method for manufacturing a semiconductor device comprising:

forming a thin film transistor over a substrate, wherein the thin film transistor comprises an active region and a gate electrode with a gate insulating film interposed therebetween;

forming a first film on an electrode provided in a chamber by a CVD method using a first gas;

installing the substrate into the chamber after forming the first film; and

forming a second film over the thin film transistor by a sputtering method using the first film as a target and a second gas in the chamber.

73. (Previously Presented) A method for manufacturing a semiconductor device according to claim 72, wherein the first gas comprises a silicide gas and nitrogen.

74. (Previously Presented) A method for manufacturing a semiconductor device according to claim 72, wherein the second gas comprises at least one selected from the group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

75. (Previously Presented) A method for manufacturing a semiconductor device according to claim 72, wherein the second film is formed at a pressure of 20 Pa or less.

76. (Previously Presented) A method for manufacturing a semiconductor device according to claim 72, wherein the second film is formed over one selected from the group consisting of a glass substrate, a plastic substrate, and an organic resin film.

77. (Canceled)

78. (Previously Presented) A method for manufacturing a semiconductor device

according to claim 73, wherein the silicide gas comprises at least one selected from the group consisting of monosilane, disilane, and trisilane.

79. (Previously Presented) A method for manufacturing a semiconductor device according to claim 72, further comprising a step of forming an EL layer and an electrode over the second film.

80. (Previously Presented) A film formation method according to claim 1, wherein the sputtering method is a sputtering method using a magnetron discharge.

81. (Previously Presented) A film formation method according to claim 7, wherein the sputtering method is a sputtering method using a magnetron discharge.

82. (Previously Presented) A method for manufacturing a semiconductor device according to claim 34, wherein the sputtering method is a sputtering method using a magnetron discharge.

83. (Previously Presented) A method for manufacturing a semiconductor device according to claim 39, wherein the sputtering method is a sputtering method using a magnetron discharge.

84. (Previously Presented) A film formation method according to claim 63, wherein the sputtering method is a sputtering method using a magnetron discharge.

85. (Previously Presented) A method for manufacturing a semiconductor device according to claim 72, wherein the sputtering method is a sputtering method using a magnetron discharge.